Unit in mm

TOSHIBA HIGH EFFICIENCY RECTIFIER (HED) SILICON EPITAXIAL JUNCTION TYPE

1 R 5 D L 4 1 A

SWITCHING TYPE POWER SUPPLY APPLICATIONS

• Repetitive Peak Reverse Voltage : V_{RRM}=200V

• Average Forward Current : $I_{F(AV)} = 1.5A (Ta = 25^{\circ}C)$

• Very Fast Reverse-Recovery Time: trr=35ns (Max.)

• Low Forward Voltage : V_{FM}=0.98V (Max.)

Available to Reduce Switching Losses and Output Noise.

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Reverse Voltage	V_{RRM}	200	V	
Average Forward Current	I _{F (AV)}	1.5	A	
Peak One Cycle Surge Forward	Ingas	60 (50Hz)	A	
Current (Non-Repetitive)	IFSM	66 (60Hz)		
Junction Temperature	T_j	-40~150	°C	
Storage Temperature	$T_{ m stg}$	-40~150	°C	

1. ANODE
2. CATHODE

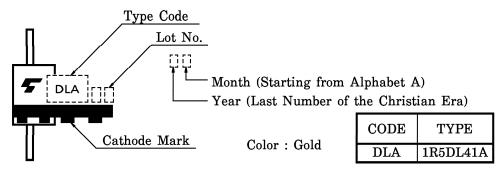
JEDEC —
EIAJ —
TOSHIBA 3-4B1A

Weight: 0.47g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

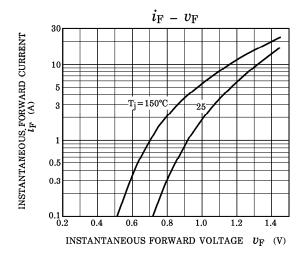
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	$V_{\mathbf{FM}}$	I _{FM} =1.5A	_	_	0.98	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 200V$	_	_	100	μ A
Reverse Recovery Time	t _{rr}	$I_F=1A$, di/dt=-30A/ μ s	_	_	35	ns
Forward Recovery Time	$t_{ m fr}$	$I_{\mathbf{F}} = 1.0 A$	_	_	100	ns
Thermal Resistance	$R_{ ext{th }(j-a)}$	Junction to Ambient	_	_	100	°C/W
Thermal Resistance	$R_{ ext{th}(j-\ell)}$	Junction to Lead		_	30	°C/W

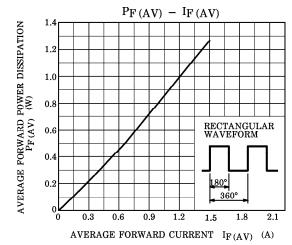
MARKING

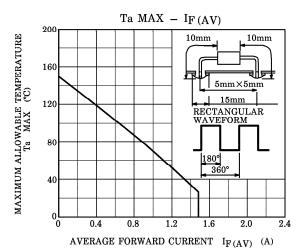


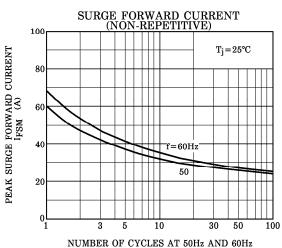
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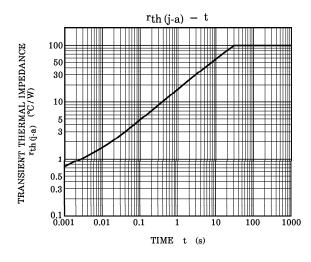
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